Vishay Siliconix

HALOGEN

FREE

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

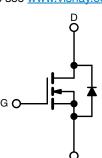


Marking code: Q042

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.00253			
I <sub>D</sub> (A) <sup>e</sup>	152			
Configuration	Single			

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- · Wettable flank terminals
- Low thermal resistance with 0.75 mm profile
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK ® 1212-8SLW
Lead (Pb)-free and halogen-free	SQS140ENW (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS ( PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	40	V	
Gate-source voltage		$V_{GS}$	± 20		
Continuous drain current e	T <sub>C</sub> = 25 °C	l <sub>D</sub>	152		
	T <sub>C</sub> = 125 °C		87		
Continuous source current (diode conduction) e		I <sub>S</sub>	108	А	
Pulsed drain current <sup>a, e</sup>		I <sub>DM</sub>	350		
Single pulse avalanche current	J 0.1 ml J	I <sub>AS</sub>	31.5		
Single pulse avalanche energy	L = 0.1 mH	E <sub>AS</sub>	49.6	mJ	
Maximum power dissipation a, e	T <sub>C</sub> = 25 °C	Б.	119	14/	
	T <sub>C</sub> = 125 °C	$P_{D}$	39	W	
Operating junction and storage temperature range Soldering recommendations (peak temperature) c		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175		
		Ü	260	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount b	R <sub>thJA</sub>	54	°C/W	
Junction-to-case (drain) <sup>d</sup>		$R_{thJC}$	1.26		

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. As per JESD51-14
- e. Values based on R<sub>thJC</sub> and T<sub>C</sub> of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0$ , $I_D = 250 \mu A$		40	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		3.0	3.5	
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	μΑ
Zero gate voltage drain current		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	20	-	-	Α
Drain-source on-state resistance a		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0021	0.00253	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.0038	Ω
	, ,	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	0.0043	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	55	-	S
Dynamic <sup>b</sup>					•		
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	2222	3111	
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		-	923	1295	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	37	52	
Total gate charge <sup>c</sup>	Qg			-	38	57	
Gate-source charge c	$Q_{gs}$	$V_{GS} = 10 \text{ V}$ $V_{DS} = 20 \text{ V}, I_D = 5 \text{ A}$	-	11	-	nC	
Gate-drain charge <sup>c</sup>	$Q_{gd}$			-	8	-	
Gate resistance	$R_g$	f = 1 MHz		0.5	1.1	1.7	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD}=20~V,~R_L=1.33~\Omega$ $I_D\cong 15~A,~V_{GEN}=10~V,~R_g=1~\Omega$		-	13	20	ns
Rise time <sup>c</sup>	t <sub>r</sub>			-	5	9	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	22	33	
Fall time <sup>c</sup>	t <sub>f</sub>			-	8	12	
Source-Drain Diode Ratings and Charac	teristic <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	350	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V		-	0.82	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 5 A, di/dt = 100 A/μs		-	38	78	ns
Body diode reverse recovery charge	$Q_{rr}$			-	34	70	nC
Reverse recovery fall time	ta			-	19	-	
Reverse recovery rise time	t <sub>b</sub>			-	20	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-1.6	-3.2	Α

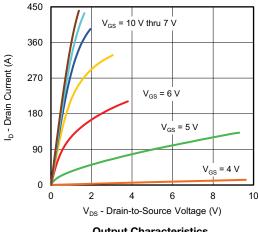
#### Notes

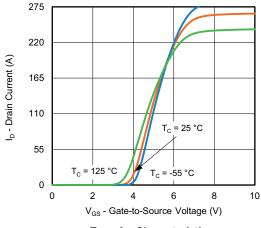
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



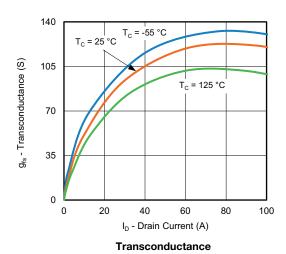
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

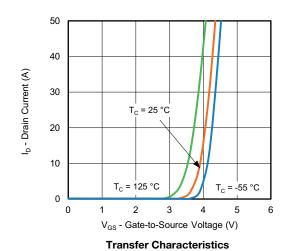


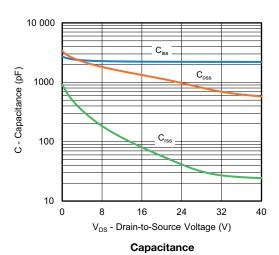


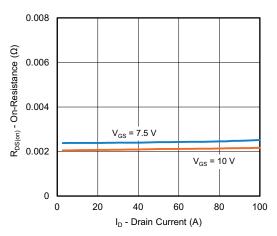
**Output Characteristics** 











On-Resistance vs. Drain Current

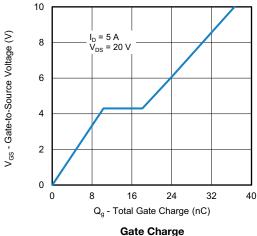
T<sub>J</sub> = 25 °C

8.0

0.6



### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Charge (nC) V<sub>SD</sub> - Source-to-Drain Voltage (V)

harge Source Drain Diode Forward Voltage

I<sub>S</sub> - Source Current (A)

100

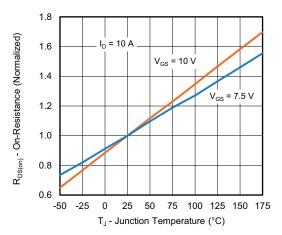
10

1

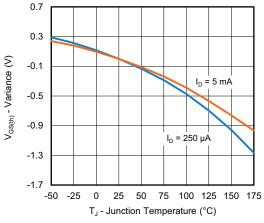
0.1

0.01

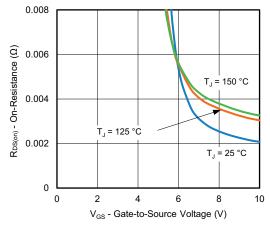
T<sub>J</sub> = 150 °C



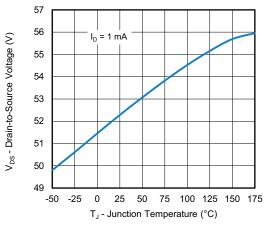
On-Resistance vs. Junction Temperature



Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

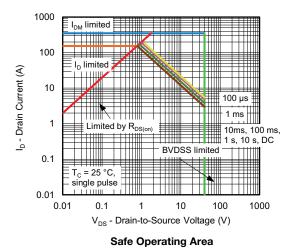


**Drain Source Breakdown vs. Junction Temperature** 

For technical questions, contact: automostech

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### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)

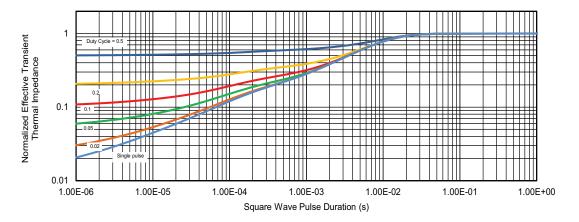


#### Note

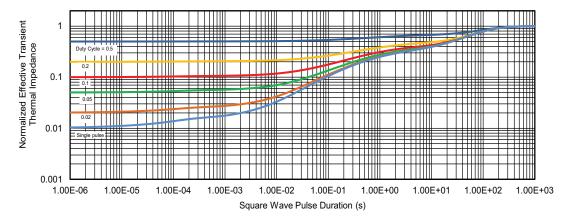
a.  $V_{GS} > \mbox{minimum} \ V_{GS}$  at which  $R_{DS(on)}$  is specified



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



#### Normalized Thermal Transient Impedance, Junction-to-Ambient

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?63038">www.vishay.com/ppg?63038</a>.



### RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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